杰力科技股份有限公司
Excelliance MOS Corporation

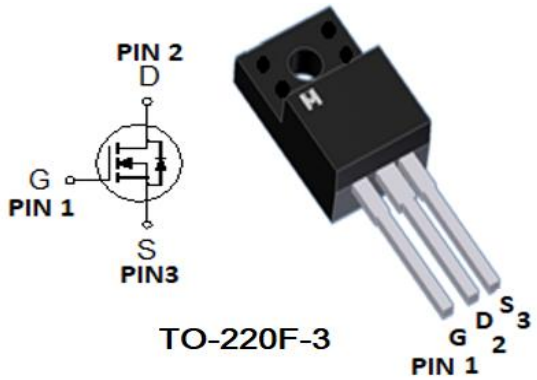
EMD04N10F

Single N-Channel Logic Level Enhancement Mode Field Effect Transistor

▪Product Summary:

	N-CH
BV_{DSS}	100V
$R_{DSON\ (MAX.)}$@V_{GS}=10V	4.5mΩ
$R_{DSON\ (MAX.)}$@V_{GS}=7V	6.0mΩ
I_D @T_C=25°C	124A
I_D @T_A=25°C	19A

▪ Pin Description:



Single N Channel MOSFET
UIS, Rg 100% Tested
RoHS & Halogen Free & TSCA Compliant

▪ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	124	A
	T_C = 100 °C		78	
Continuous Drain Current	T_A = 25 °C	I_D	19	
	T_A = 70 °C		15	
Pulsed Drain Current[1]		I_{DM}	76	
Avalanche Current		I_{AS}	108	
Avalanche Energy	L = 0.1mH	EAS	583.2	mJ
Repetitive Avalanche Energy[2]	L = 0.05mH	EAR	291.6	
Power Dissipation	T_C = 25 °C	P_D	125	W
	T_C = 100 °C		50	
Power Dissipation	T_A = 25 °C	P_D	3	W
	T_A = 70 °C		2	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

▪ 100% UIS testing in condition of VD=50V, L=0.1mH, VG=10V, IL= 65A, Rated VDS=100V N-CH

▪THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case		$R_{\theta JC}$		1	°C/W
Junction-to-Ambient[3]	t≦10s	$R_{\theta JA}$		24	
	Steady-State	$R_{\theta JA}$		41	

[1]Pulse width limited by maximum junction temperature.
[2]Duty cycle < 1%
[3]41°C / W when mounted on a 1 in^2 pad of 2 oz copper.
[4]Guarantee by Engineering test

▪**ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage[4]	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100			V
Gate Threshold Voltage[4]	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	3	4	
Gate-Body Leakage[4]	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current[4]	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1	μA
		V_{DS} =70V, V_{GS} =0V, T_J = 125 °C			25	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 10V, V_{GS} = 10V	124			A
Drain-Source On-State Resistance[1,4]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 20A		3.5	4.5	mΩ
		V_{GS} = 7V, I_D = 20A		4.0	6.0	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A		90		S
DYNAMIC						
Input Capacitance[5]	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz		5738		pF
Output Capacitance[5]	C_{oss}			1105		
Reverse Transfer Capacitance[5]	C_{rss}			70		
Gate Resistance[4,5]	R_g	f = 1MHz		0.7		Ω
Total Gate Charge[1,2,5]	Q_g(V_{GS}=10V)	V_{DS} = 50V, V_{GS} = 10V, I_D = 20A		85		nC
	Q_g(V_{GS}=7V)			62		
Gate-Source Charge[1,2,5]	Q_{gs}			28		
Gate-Drain Charge[1,2,5]	Q_{gd}			16		
Turn-On Delay Time[1,2,5]	$t_{d(on)}$	V_{DS} = 50V, V_{GS} = 10V, I_D = 5A , Rg = 6Ω		24.3		nS
Rise Time[1,2,5]	t_r			25.4		
Turn-Off Delay Time[1,2,5]	$t_{d(off)}$			64.1		
Fall Time[1,2,5]	t_f			66.6		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Continuous Current	I_S				124	A
Pulsed Current[3]	I_{SM}				76	
Forward Voltage[1,4]	V_{SD}	I_F = 30A, V_{GS} = 0V			1.2	V
Reverse Recovery Time[5]	t_{rr}	I_F = 30A, dI_F/dt = 100A / μS		92.9		nS
Peak Reverse Recovery Current[5]	$I_{RM(REC)}$			-2.92		A
Reverse Recovery Charge[5]	Q_{rr}			153.5		nC

[1]Pulse test : Pulse Width ≦ 300 usec, Duty Cycle ≦ 2%.

[2]Independent of operating temperature.

[3]Pulse width limited by maximum junction temperature.

[4]Guarantee by FT test Item

[5]Guarantee by Engineering test

EMC will review datasheet by quarter, and update new version.

▪TYPICAL CHARACTERISTICS

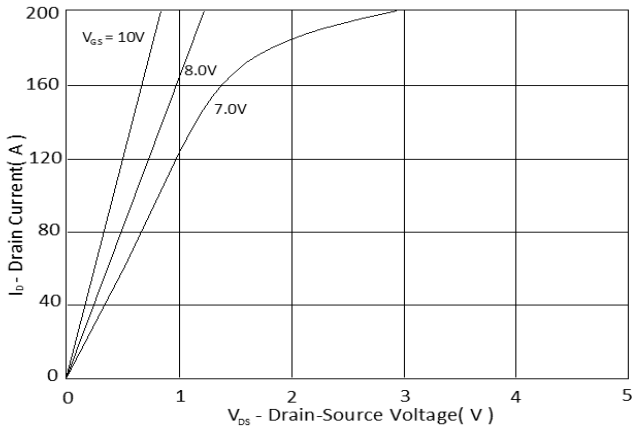


Fig.1 Typical Output Characteristics

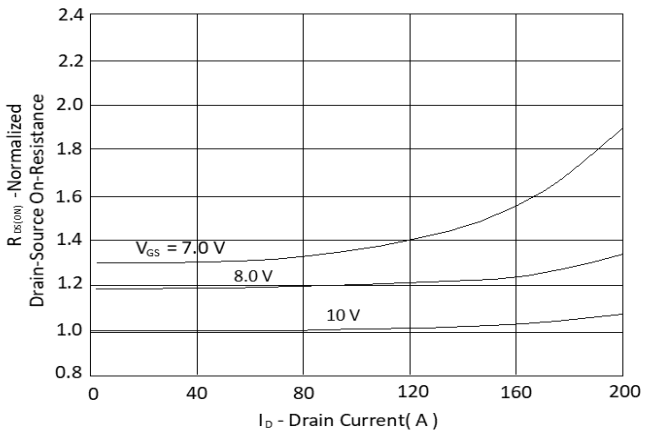


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

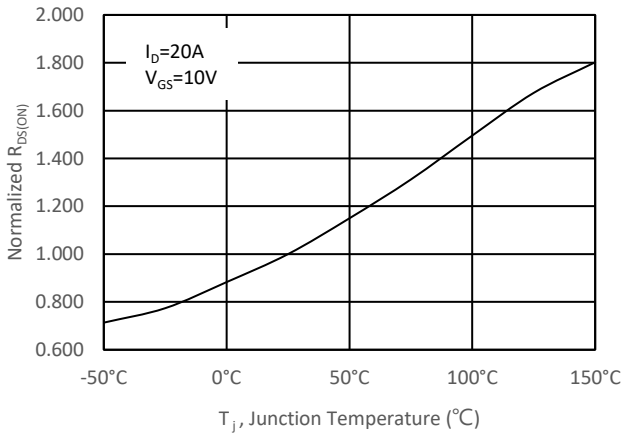


Fig.3 Normalized On-Resistance v.s. Junction Temperature

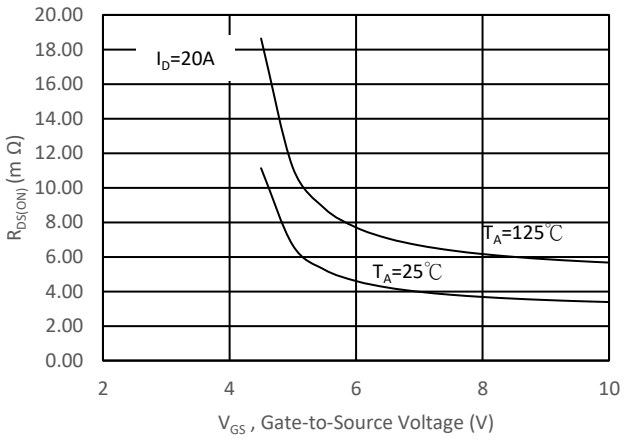


Fig.4 On-Resistance v.s. Gate Voltage

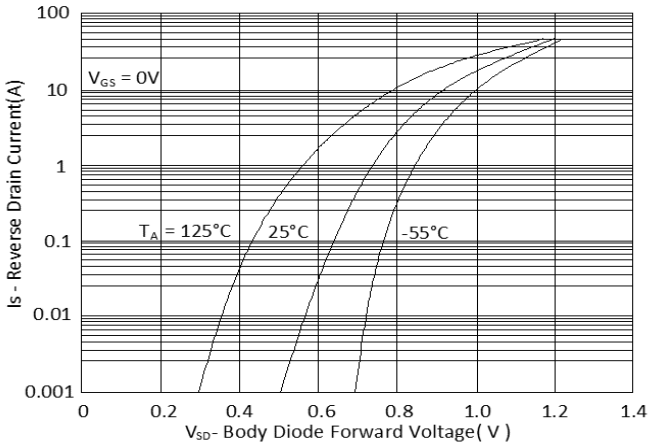


Fig.5 Forward Characteristic of Reverse Diode

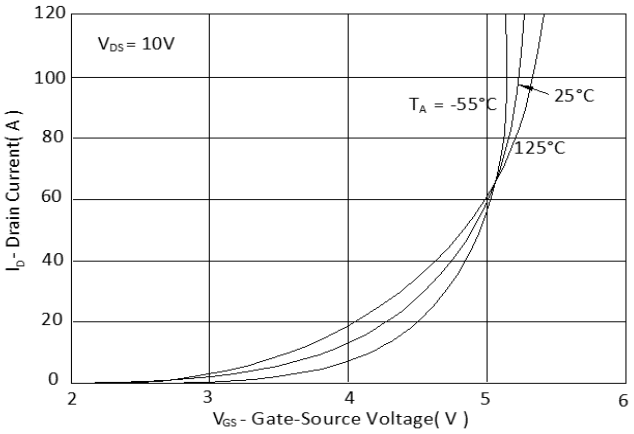


Fig.6 Transfer Characteristics

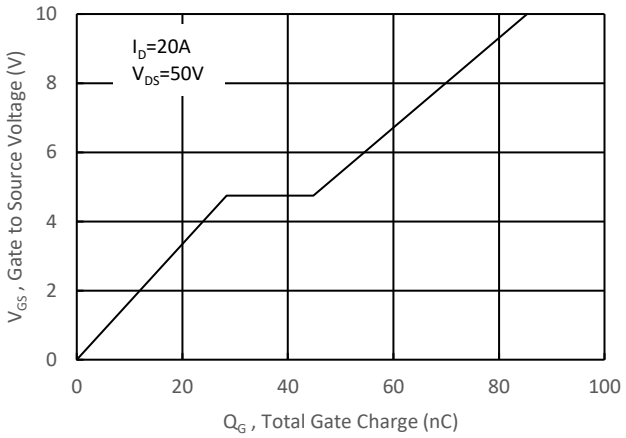


Fig.7 Gate Charge Characteristics

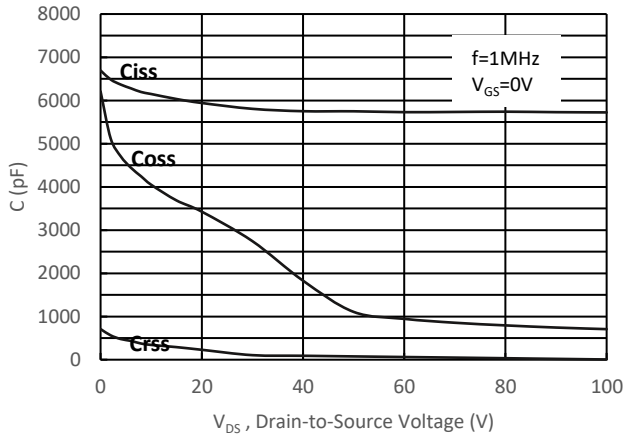


Fig.8 Typical Capacitance Characteristics

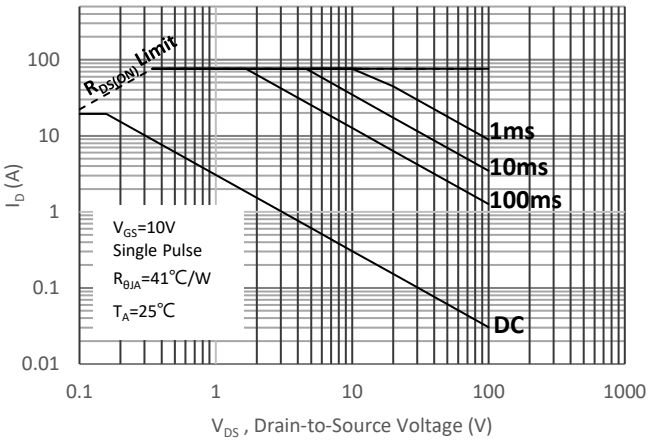


Fig 9. Maximum Safe Operating Area

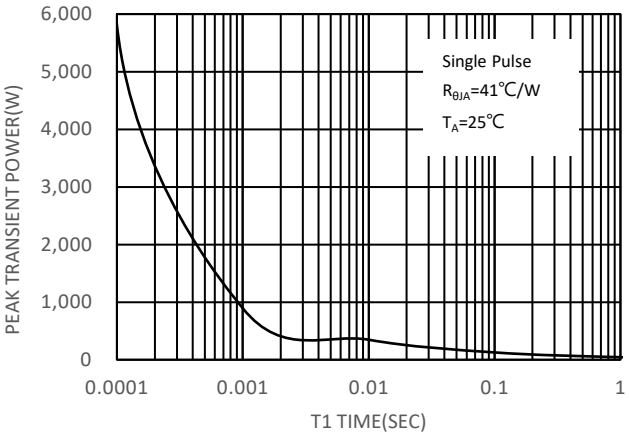


Fig 10. Single Pulse Maximum Power Dissipation

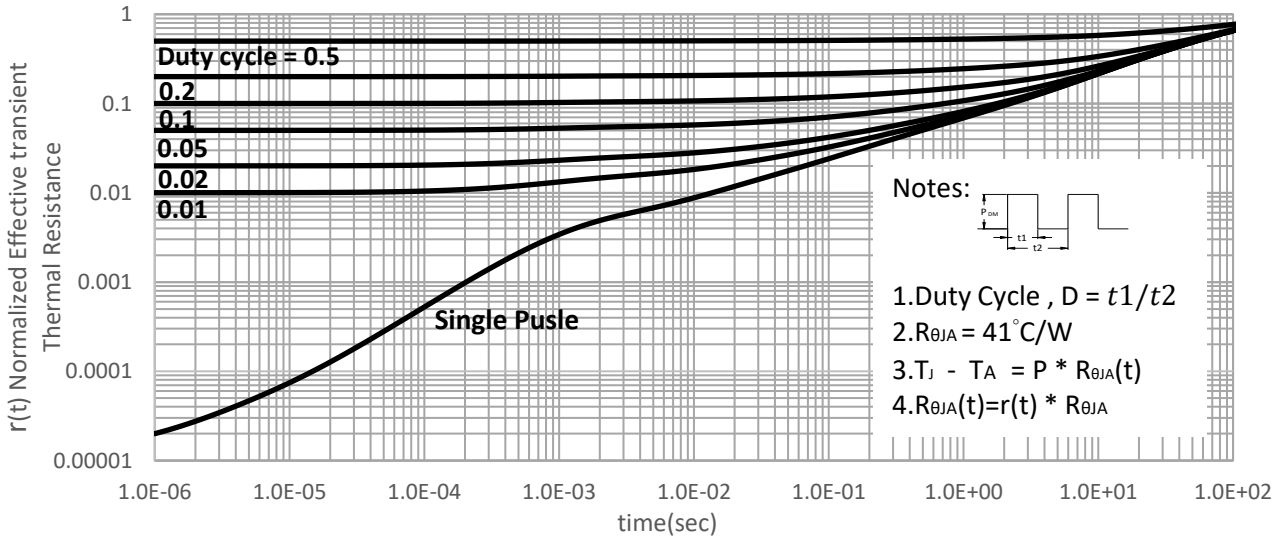
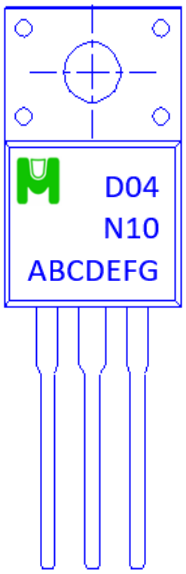


Fig 11. Effective Transient Thermal Impedance

Ordering & Marking Information:

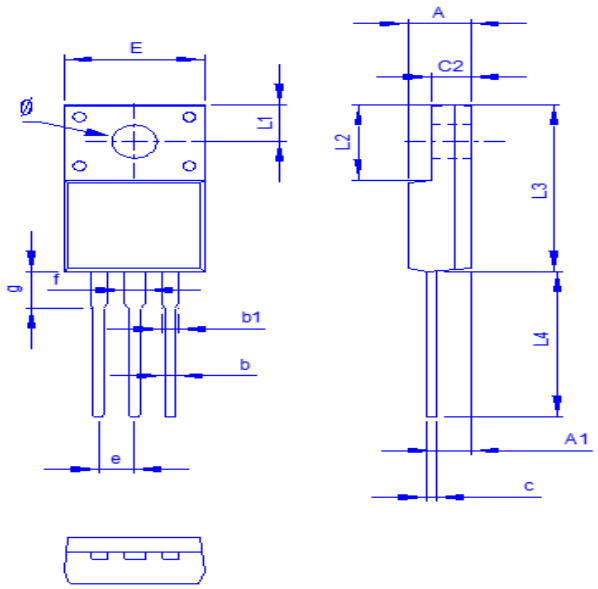
Device Name: EMD04N10F for TO-220F-3



D04N10: Device Name

ABCDEFG: Date Code
A: Assembly House
B: Year(A:2008 B:2009 C:2010….)
C: Month(A:01 B:02 C:03 D:04 E:05 F:06 G:07 H:08 I:09 J:10 K:11 L:12)
DEFG: Serial No.

Outline Drawing



Dimension	A	A1	b	b1	c	c2	E	L1	L2	L3	L4	ø	e
Min.	4.3	2.49	0.5	1.1	0.4	2.34	9.96	2.7	6.48	14.8	12.65	3	2.44
Typ.	4.5	2.59	0.8	1.3	0.5	2.54	10.1	3.25	6.68	15.87	12.98	3.1	2.54
Max.	4.9	2.96	0.95	1.6	0.75	3.2	10.36	3.45	6.9	16.2	13.5	3.38	2.64

Dimension	f	g
Min.	1.17	2.93
Typ.	1.28	3.03
Max.	1.75	4

◆ **Tube Information:50pcs/Tube (1000pcs/Box)**